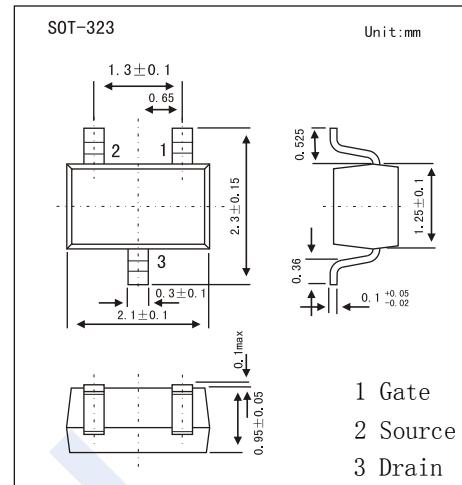


## P-Channel MOSFET

## KI001PW

## ■ Features

- $V_{DS} (V) = -15V$
- $I_D = -3 A$  ( $V_{GS} = -10V$ )
- $R_{DS(ON)} < 85m\Omega$  ( $V_{GS} = -4.5V$ )
- $R_{DS(ON)} < 95m\Omega$  ( $V_{GS} = -2.5V$ )

■ Absolute Maximum Ratings  $T_a = 25^\circ C$ 

Parameter	Symbol	Rating	Unit
Drain-Source Voltage	$V_{DS}$	-15	V
Gate-Source Voltage	$V_{GS}$	$\pm 12$	
Continuous Drain Current	$I_D$	-3	A
Power Dissipation	$P_D$	0.2	W
Junction Temperature	$T_J$	150	$^\circ C$
Junction Storage Temperature Range	$T_{stg}$	-55 to 150	

■ Electrical Characteristics  $T_a = 25^\circ C$ 

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Drain-Source Breakdown Voltage	$V_{DSS}$	$I_D = -250 \mu A, V_{GS} = 0V$	-15			V
Zero Gate Voltage Drain Current	$I_{DSS}$	$V_{DS} = -15V, V_{GS} = 0V, T_J = 25^\circ C$			-1	$\mu A$
Gate-Body leakage current	$I_{GSS}$	$V_{DS} = 0V, V_{GS} = \pm 10V$			$\pm 100$	nA
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = -250 \mu A$	-0.4		-1	V
Static Drain-Source On-Resistance	$R_{DS(on)}$	$V_{GS} = -4.5V, I_D = -3A$			85	$m\Omega$
		$V_{GS} = -2.5V, I_D = -2A$			95	

## ■ Marking

Marking	001P
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